Taha Ayari

List of Publications by Year
in descending order

12	313	1163117 8	1281871 11
papers	citations	h-index	g-index

12	12	12	533
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Large-Area Two-Dimensional Layered Hexagonal Boron Nitride Grown on Sapphire by Metalorganic Vapor Phase Epitaxy. Crystal Growth and Design, 2016, 16, 3409-3415.	3.0	106
2	Wafer-scale controlled exfoliation of metal organic vapor phase epitaxy grown InGaN/GaN multi quantum well structures using low-tack two-dimensional layered h-BN. Applied Physics Letters, 2016, 108, .	3.3	74
3	Gas sensors boosted by two-dimensional h-BN enabled transfer on thin substrate foils: towards wearable and portable applications. Scientific Reports, 2017, 7, 15212.	3.3	54
4	Heterogeneous Integration of Thin-Film InGaN-Based Solar Cells on Foreign Substrates with Enhanced Performance. ACS Photonics, 2018, 5, 3003-3008.	6.6	20
5	Largeâ€Area van der Waals Epitaxial Growth of Vertical IIIâ€Nitride Nanodevice Structures on Layered Boron Nitride. Advanced Materials Interfaces, 2019, 6, 1900207.	3.7	12
6	Effectiveness of selective area growth using van der Waals h-BN layer for crack-free transfer of large-size III-N devices onto arbitrary substrates. Scientific Reports, 2020, 10, 21709.	3.3	12
7	Novel Scalable Transfer Approach for Discrete IIIâ€Nitride Devices Using Waferâ€Scale Patterned hâ€BN/Sapphire Substrate for Pickâ€andâ€Place Applications. Advanced Materials Technologies, 2019, 4, 1900164.	5.8	10
8	MOVPE of GaN-based mixed dimensional heterostructures on wafer-scale layered 2D hexagonal boron nitrideâ€"A key enabler of III-nitride flexible optoelectronics. APL Materials, 2021, 9, .	5.1	9
9	MOVPE van der Waals epitaxial growth of AlGaN/AlGaN multiple quantum well structures with deep UV emission on large scale 2D h-BN buffered sapphire substrates. Journal of Crystal Growth, 2019, 507, 352-356.	1.5	8
10	Nanopyramid-based absorber to boost the efficiency of InGaN solar cells. Solar Energy, 2019, 190, 93-103.	6.1	7
11	Lightâ€Emitting Diodes: Largeâ€Area van der Waals Epitaxial Growth of Vertical IIIâ€Nitride Nanodevice Structures on Layered Boron Nitride (Adv. Mater. Interfaces 16/2019). Advanced Materials Interfaces, 2019, 6, 1970102.	3.7	1
12	Heterogeneous Integration: Novel Scalable Transfer Approach for Discrete IIIâ€Nitride Devices Using Waferâ€Scale Patterned hâ€BN/Sapphire Substrate for Pickâ€andâ€Place Applications (Adv. Mater. Technol.) Tj ET Q q 0 0 0 rg BT /Overlo	6.8	0